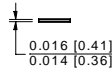
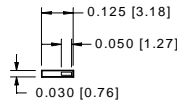


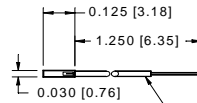


#### PACKAGE DIMENSIONS INCH (mm)

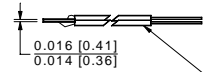


BARECHIP

ACTIVE AREA = 1.0 mm<sup>2</sup>  
PDB-C601-1  
PDB-V601-1



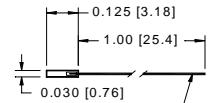
ANODE, RED WIRE



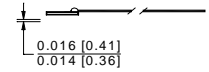
CATHODE, BLACK WIRE

30 GAGE P.V.C. WIRE

PDB-C601-2  
PDB-V601-2



ANODE, BUSS WIRE



34 GAGE BUSS WIRE

PDB-C601-3  
PDB-V601-3

#### FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

#### DESCRIPTION:

Low cost blue enhanced planar diffused silicon solderable photodiode. The **PDB-V601** cell is designed for low noise, photovoltaic applications. The **PDB-C601** cell is designed for low capacitance, high speed, photoconductive operation. They are available bare, PVC or buss wire leads.

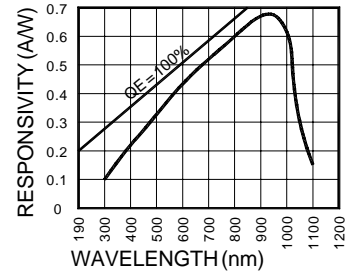
#### APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

#### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	PDB-C601		PDB-V601		UNITS
		MIN	MAX	MIN	MAX	
V <sub>BR</sub>	Reverse Voltage		75		25	V
T <sub>STG</sub>	Storage Temperature	-40	+125	-40	+125	°C
T <sub>O</sub>	Operating Temperature Range	-40	+100	-40	+100	°C
T <sub>S</sub>	Soldering Temperature		+224		+224	°C
I <sub>L</sub>	Light Current		500		500	mA

#### SPECTRAL RESPONSE



#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	PDB-C601			PDB-V601			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	15	17		10	13		μA
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 5 V*		.5	2		3	7	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	60	150		100	250		MΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8			-8		% / °C
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 5 V**		10			250		pF
λ <sub>range</sub>	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λ <sub>p</sub>	Spectral Response - Peak	Spot Scan		940			940		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	25	50		5	15		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 0 V @ Peak	1 x 10 <sup>-14</sup> TYP			2 x 10 <sup>-14</sup> TYP			W / √Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 5 V**		10			300		nS

\*V<sub>R</sub> = 100 mV on Photovoltaic type \*\*V<sub>R</sub> = 0 V on Photoconductive type

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.